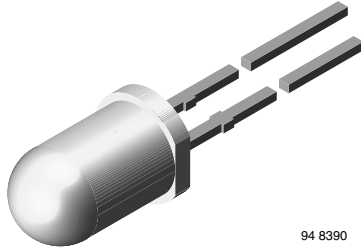


High Speed Infrared Emitting Diode, RoHS Compliant, 890 nm, GaAIAs Double Hetero



94 8390

DESCRIPTION

TSHF5210 is an infrared, 890 nm emitting diode in GaAIAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm): \varnothing 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 890$ nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity: $\varphi = \pm 10^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- High modulation bandwidth: $f_c = 12$ MHz
- Good spectral matching with Si photodetectors
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC


RoHS
COMPLIANT

APPLICATIONS

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK - coded, 450 kHz or 1.3 MHz)
- Smoke-automatic fire detectors

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	φ (deg)	λ_p (nm)	t_r (ns)
TSHF5210	180	± 10	890	30

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHF5210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 $\frac{3}{4}$

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I_{FM}	200	mA
Surge forward current	$t_p = 100 \mu s$	I_{FSM}	1.5	A
Power dissipation		P_V	160	mW

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Junction temperature		T_j	100	°C
Operating temperature range		T_{amb}	- 40 to + 85	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	230	K/W

Note

$T_{amb} = 25$ °C, unless otherwise specified

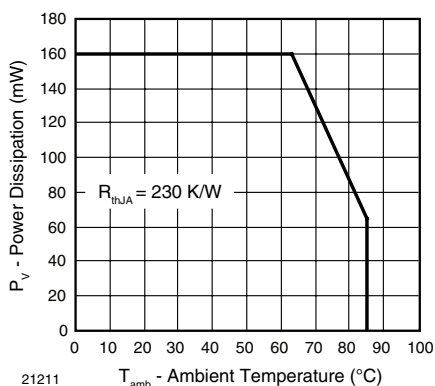


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

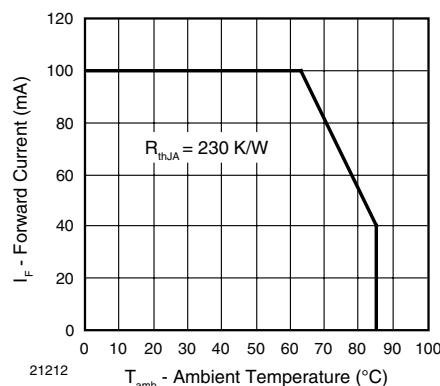


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100$ mA, $t_p = 20$ ms	V_F		1.4	1.6	V
	$I_F = 1$ A, $t_p = 100$ μ s	V_F		2.3		V
Temperature coefficient of V_F	$I_F = 1$ mA	TK_{V_F}		- 1.8		mV/K
Reverse current	$V_R = 5$ V	I_R			10	μ A
Junction capacitance	$V_R = 0$ V, $f = 1$ MHz, $E = 0$	C_j		125		pF
Radiant intensity	$I_F = 100$ mA, $t_p = 20$ ms	I_e	120	180	360	mW/sr
	$I_F = 1$ A, $t_p = 100$ μ s	I_e		1800		mW/sr
Radiant power	$I_F = 100$ mA, $t_p = 20$ ms	ϕ_e		50		mW
Temperature coefficient of ϕ_e	$I_F = 100$ mA	TK_{ϕ_e}		- 0.35		%/K
Angle of half intensity		ϕ		± 10		deg
Peak wavelength	$I_F = 100$ mA	λ_p		890		nm
Spectral bandwidth	$I_F = 100$ mA	$\Delta\lambda$		40		nm
Temperature coefficient of λ_p	$I_F = 100$ mA	TK_{λ_p}		0.25		nm/K
Rise time	$I_F = 100$ mA	t_r		30		ns
Fall time	$I_F = 100$ mA	t_f		30		ns
Cut-off frequency	$I_{DC} = 70$ mA, $I_{AC} = 30$ mA pp	f_c		12		MHz
Virtual source diameter		d		3.7		mm

Note

$T_{amb} = 25$ °C, unless otherwise specified

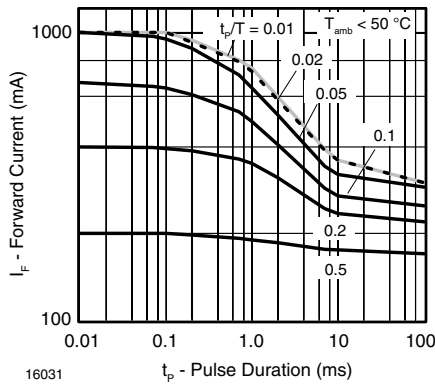
BASIC CHARACTERISTICS
 $T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified


Fig. 3 - Pulse Forward Current vs. Pulse Duration

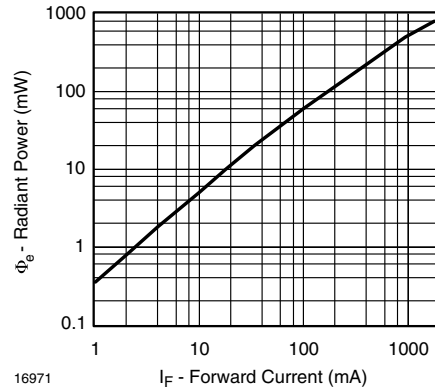


Fig. 6 - Radiant Power vs. Forward Current

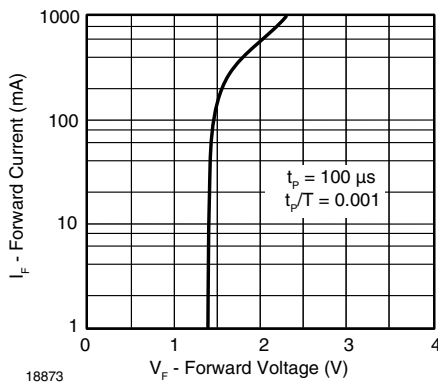


Fig. 4 - Forward Current vs. Forward Voltage

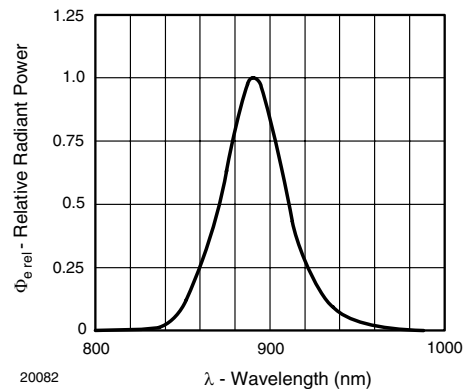


Fig. 7 - Relative Radiant Power vs. Wavelength

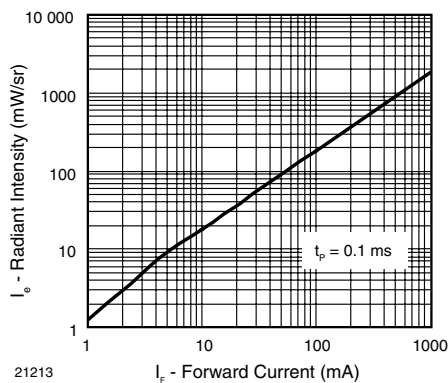


Fig. 5 - Radiant Intensity vs. Forward Current

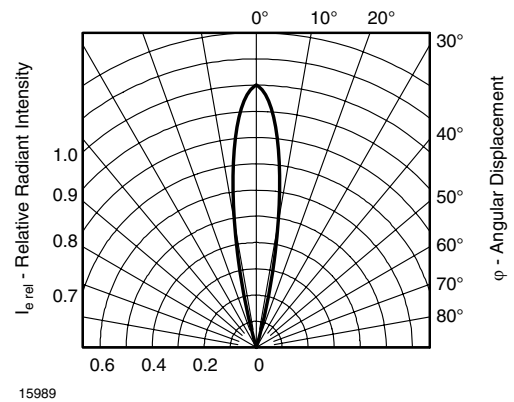


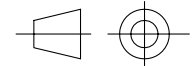
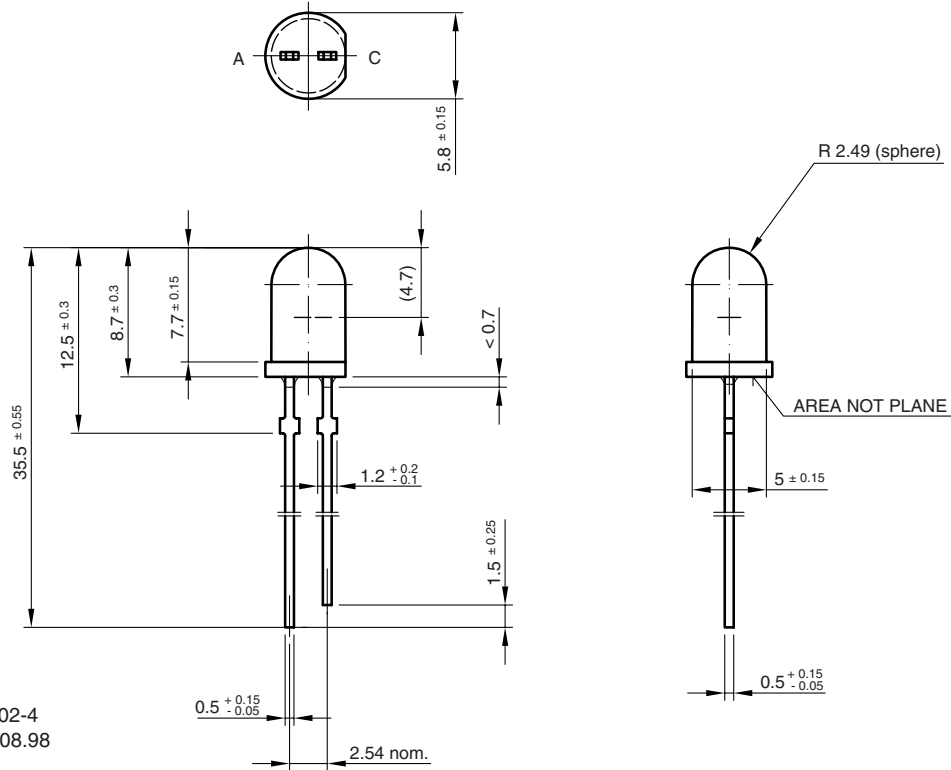
Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

TSHF5210

Vishay Semiconductors High Speed Infrared Emitting Diode, RoHS Compliant, 890 nm, GaAlAs Double Hetero



PACKAGE DIMENSIONS in millimeters



technical drawings according to DIN specification

6.544-5258.02-4
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95 10916



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